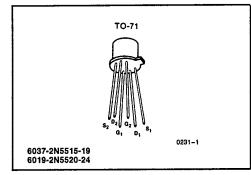
#### G E SOLID STATE

# **2N551** Dual N-C Low Nois FEATURES • Tight Temperatu • Tight Matching 2N5515-2N5524 **Dual N-Channel JFET** Low Noise Amplifier

- Tight Temperature Tracking
- High Common Mode Rejection
- Low Noise

#### PIN CONFIGURATION





#### **ABSOLUTE MAXIMUM RATINGS**

$(T_{\Delta} = 25^{\circ}C \text{ unless otherwise specified})$	
Gate-Source or Gate-Drain Voltage	-40V
Gate Current (Note 1)	50mA
Storage Temperature Range65°C to +	200°C
Operating Temperature Range55°C to +	150°C
Lead Temperature (Soldering, 10sec)+:	300°C

	One Side	<b>Both Sides</b>
Power Dissipation (TA=85°C)	250mW	375mW
Derate above 25°C	2.0mW/°C	3.0mW/°C

NOTE: Per transistor.

NOTE: Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions above those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

#### **ORDERING INFORMATION**

TO-72	
2N5515	
2N5516	
2N5517	
2N5518	
2N5519	
2N5520	
2N5521	
2N5522	
2N5523	
2N5524	

۰...

#### ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25°C unless otherwise specified)

Symbol	Parameter	Parameter Test Conditions		Min	Max	Units
IGSS	Gate Reverse Current	$V_{GS} = -30V, V_{DS} = 0$			- 250	pА
			T <sub>A</sub> =150°C		-250	nA
BVGSS	Gate-Source Breakdown Voltage	$I_G = -1 \mu A, V_{DS} = 0$	-40	_	v	
VP	Gate-Source Pinch-Off Voltage	V <sub>DS</sub> ⇔20V, I <sub>D</sub> =1nA	-0.7	-4		
IDSS	Drain Current at Zero Gate Voltage (Note 1)	$V_{DS} = 20V, V_{GS} = 0$		0.5	7.5	mA
9fs	Common-Source Forward Transconductance (Note 1)		f=1kHz	1000	4000	μs
goss	Common-Source Output Conductance				10	
C <sub>rss</sub>	Common-Source Reverse Transfer Capacitance (Note 3)		f=1MHz		5	pF
Ciss	Common-Source Input Capacitance (Note 3)				25	

INTERSIL'S SOLE AND EXCLUSIVE WARRANTY OBLIGATION WITH RESPECT TO THIS PRODUCT SHALL BE THAT STATED IN THE WARRANTY ARTICLE OF THE CONDITION OF SALE. THE WARRANTY SHALL BE EXCLUSIVE AND SHALL BE IN LIEU OF ALL OTHER WARRANTIES, EXPRESS, IMPLIED OR STATUTORY, INCLUDING THE IMPLIED WARRANTIES OF MERCHANTABILITY AND FITNESS FOR A PARTICULAR USE.

NOTE: All typical values have been characterized but are not tested

10-52

## G E SOLID STATE

### 2N5515-2N5524

# 01 DE 3875081 0011005 6

#### **ELECTRICAL CHARACTERISTICS** (Continued) ( $T_A = 25^{\circ}C$ unless otherwise specified)

2N5515-2N5524 ELECTRICAL CHARACTERISTICS (Continued) (T <sub>A</sub> = 25°C unless otherwise specified)								
Symbol	Parameter	Test Conditio	008	Min	Max	Units		
ēn	Equivalent Input Noise Voltage (Note 3)	2N5515-19		f=10Hz		30		
		2N5520-24				15	nV/√Hz	
		2N5515-24	]	f=1kHz		10		
l <sub>G</sub>	Gate Current	$V_{DG} = 20V, I_D = 200 \mu A$			-100	pА		
.u				T <sub>A</sub> =125°C		-100	nA	
V <sub>GS</sub>	Gate Source Voltage		]		-0.2	-3.8	V	
9fs	Common-Source Forward Transconductance (Note 1)			f=1kHz	500	1000	μs	
goss	Common-Source Output Conduc	1			1	μs		

#### MATCHING CHARACTERISTICS (T<sub>A</sub> = 25°C unless otherwise specified)

											-		
Symbol	Parameter	Test Conditions	2N5515,20 2N5516,21		2N5517,22 2N55		518,23 2N5		19,24	Unite			
			Min	Max		Max	f			Max	Min	Max	
IDSS1/IDSS2	Drain Current Ratio at Zero Gate Voltage (Note 1)	V <sub>DS</sub> =20V, V <sub>GS</sub> ≕0	0.95	1	0.95	1	0.95	1	0.95	1	0.90	1	
<sub>G1</sub> –   <sub>G2</sub>	Differential Gate Current (+ 125°C)	V <sub>DG</sub> =20V, I <sub>D</sub> =200μA		10		10		10		10		10	nA
g <sub>fs1</sub> /g <sub>fs2</sub>		V <sub>DG</sub> =20V, I <sub>D</sub> =200μA f=1kHz	0.97	1	0.97	1	0.95	1	0.95	1	0.90	1	
goss1 - goss2	Differential Output Conductance	V <sub>DG</sub> = 20V, I <sub>D</sub> ≕ 200μA f = 1kHz		0.1		0.1		0.1		0.1		0.1	μs
V <sub>GS1</sub> – V <sub>GS2</sub>	Differential Gate-Source Voltage	V <sub>DG</sub> =20V, I <sub>D</sub> =200μA		5		5		10		15		15	mV
Δ V <sub>GS1</sub> – V <sub>GS2</sub> ΔΤ	Gate-Source Voltage Differential Drift (T <sub>A</sub> = -55°C to +125°C)	V <sub>DG</sub> =20V, I <sub>D</sub> =200μA		5		10		20		40		80	<u>μ</u> ∨ ℃
CMRR		$V_{DD} = 10 \text{ to } 20V,$ $I_D = 200 \mu \text{A}$	100		100		90						dB



**NOTES: 1.** Pulse duration of 28ms used during test. **2.** CMRR = 20  $\log_{10}\Delta V_{DD}/\Delta i V_{GS1} - V_{GS2}$ l, ( $\Delta V_{DD} = 10V$ ) **3.** For design reference only, not 100% tested.

INTERSIL'S SOLE AND EXCLUSIVE WARRANTY OBLIGATION WITH RESPECT TO THIS PRODUCT SHALL BE THAT STATED IN THE WARRANTY ARTICLE OF THE CONDITION OF SALE. THE WARRANTY SHALL BE EXCLUSIVE AND SHALL BE IN LIEU OF ALL OTHER WARRANTIES, EXPRESS, IMPLIED OR STATUTORY, INCLUDING THE IMPLIED WARRANTIES OF MERCHANTABILITY AND FITNESS FOR A PARTICULAR USE.

NOTE: All typical values have been charactenzed but are not tested.

10-53

Copyright © Each Manufacturing Company.

All Datasheets cannot be modified without permission.

This datasheet has been download from :

www.AllDataSheet.com

100% Free DataSheet Search Site.

Free Download.

No Register.

Fast Search System.

www.AllDataSheet.com